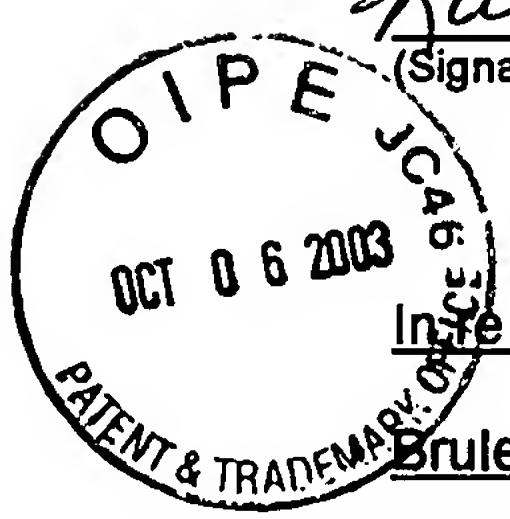


I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to : Commissioner of Patents and Trademarks, Washington, D.C. 20231, on October 3, 2003. The applicant and/or attorney requests the date of deposit as the filing date. Depositor: Karen Cinq-Mars

Karen Cinq-Mars 10/3/03
(Signature & date)



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of : October 3, 2003
Bruley, et al. : Group Art Unit:
Serial No. 10/605,128 : Examiner:
Filed: 9/10/2003 : International Business Machines Corporation
2070 Route 52
Hopewell Junction, NY 12533

TITLE: CAPACITOR AND FABRICATION METHOD USING ULTRA-HIGH VACUUM CVD OF SILICON

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the non-US patents and publications as listed on Form PTO-1449, attached hereto.

In citing these documents, no representation is made nor intended as to the pertinency or non-pertinency of the art, that better art than that listed is not available, or that other art is not applicable.

No fee is believed to be due for this submission. If any fees are required, however, the Commissioner is hereby authorized to charge such fees to Deposit Account No. 09-0458.

Respectfully submitted,
Bruley, et al.

By Margaret A. Pepper
Margaret A. Pepper
Registration No. 45,008
Telephone No. 845-894-4713



~~INFORMATION DISCLOSURE CITATION~~

(Use several sheets if necessary)

Docket Number (Optional)

FIS920030230US1

Application Number

Applicant(s)

Bruley et al.

Filing Date

Group Art Unit

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

		American Institute of Physics, Volume 81, Number 14, September 30 2002, "Bonding States and Electrical Properties of Ultrathin HfO _x N _y Gate Dielectrics," Kang et al., pp. 2593-2595.
		2002 Symposium On VLSI Technology Digest of Technical Papers, "Advanced CMOS Transistors with a Novel HfSiON Gate Dielectric," Rotondaro et al., pp. 148-149.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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2002 American Institute of Physics, Volume 80, Number 17, April 29, 2002, "Application of HfSiON as a Gate Dielectric Material," Visokay et al., pp. 3183-3185.

Journal of the Korean Physical Society, Volume 37, Number 6, December 2000, "Electrical Characteristics of AlOxNy Prepared by Oxidation of Sub-10-nm-thick AlN Films for MOS Gate Dielectric Applications," Jeon et al., pp. 886-888.

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